NOT RECOMMENDED FOR NEW DESIGN **USE DSS4160V**





DNLS160V

LOW V_{CE(SAT)} NPN SURFACE MOUNT TRANSISTOR

Features

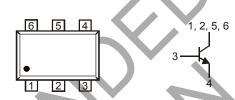
- **Epitaxial Planar Die Construction**
- Complementary PNP Type Available (DPLS160V)
- Surface Mount Package Suited for Automated Assembly
- Ultra-Small Surface Mount Package
- Lead Free/RoHS Compliant (Note 1)
- "Green Device" (Note 2)
- Qualified to AEC-Q 101 Standards for High Reliability

Mechanical Data

- Case: SOT-563
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020D
- Terminals: Finish Matte Tin annealed over Copper leadframe. Solderable per MIL-STD-202, Method 208
- Marking Information: See Page 4
- Ordering Information: See Page 4
- Weight: 0.003 grams (approximate)



SOT-563



Maximum Ratings @TA = 25°C unless otherwise specified

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V _{CBO}	80	V
Collector-Emitter Voltage	$V_{\sf CEO}$	60	V
Emitter-Base Voltage	V_{EBO}	5	V
Collector Current - Continuous	lc	1	Α
Peak Pulse Collector Current	I _{CM}	2	Α
Base Current (DC)	I _B	300	mA

Thermal Characteristics

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 3) @ T _A = 25°C	P_D	300	mW
Thermal Resistance, Junction to Ambient (Note 3) @ T _A = 25°C	$R_{ hetaJA}$	417	°C/W
Operating and Storage Temperature Range	T_J , T_{STG}	-55 to +150	°C

Notes:

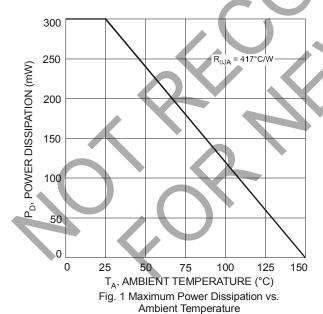
- No purposefully added lead.
- Diode's Inc.'s "Green" policy can be found on our website at http://www.diodes.com/products/lead_free/index.php.
- Device mounted on FR-4 PCB, 1 inch x 0.85 inch x 0.062 inch, pad layout as shown on page 4 or in Diodes Inc. suggested pad layout document P02001, which can be found on our website at http://www.diodes.com/datasheets/ap02001.pdf.

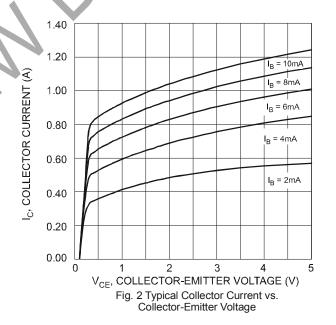


Electrical Characteristics @TA = 25°C unless otherwise specified

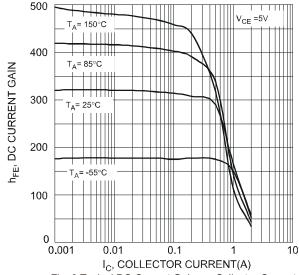
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 4)						
Collector-Base Breakdown Voltage	V _{(BR)CBO}	80	_		V	$I_C = 100 \mu A, I_E = 0$
Collector-Emitter Breakdown Voltage	V _{(BR)CEO}	60	_		V	$I_C = 10 \text{mA}, I_B = 0$
Emitter-Base Breakdown Voltage	V _{(BR)EBO}	5	_	_	V	$I_E = 100 \mu A, I_C = 0$
Collector Cutoff Current	1			100	nA	$V_{CB} = 60V, I_{E} = 0$
Collector Cuton Current	I _{CBO}		_	50	μΑ	$V_{CB} = 60V, I_E = 0, T_A = 150$ °C
Collector Cutoff Current	I _{CES}			100	nA	$V_{CE} = 60V, V_{BE} = 0$
Emitter Cutoff Current	I _{EBO}	_	_	100	nA	$V_{EB} = 5V, I_{C} = 0$
ON CHARACTERISTICS (Note 4)						
		250	320	_		$V_{CE} = 5V$, $I_C = 1mA$
DC Current Gain	h _{FE}	200	280	_	V	$V_{CE} = 5V, I_{C} = 500mA$
		100	165	_	- 4	V _{CE} = 5V, I _C = 1A
		_	80	110		$I_C = 100 \text{mA}, I_B = 1 \text{mA}$
Collector-Emitter Saturation Voltage	V _{CE(SAT)}	_	80	140	mV	$I_C = 500 \text{mA}, I_B = 50 \text{mA}$
	, ,	_	140	250		$I_C = 1A$, $I_B = 100mA$
Collector-Emitter Saturation Resistance	R _{CE(SAT)}	_	140	250	mΩ	$I_C = 1A$, $I_B = 100mA$
Base-Emitter Saturation Voltage	V _{BE(SAT)}		0.91	1.1	V	$I_C = 1A$, $I_B = 50mA$
Base-Emitter Turn On Voltage	V _{BE(ON)}	_	0.81	0.9	V	$V_{CE} = 5V$, $I_C = 1A$
SMALL SIGNAL CHARACTERISTICS						
Output Capacitance	C _{obo}	_	7	10	pF	$V_{CB} = 10V, f = 1.0MHz$
Current Gain-Bandwidth Product	f_{T}	150 🍙	270		MHz 🏽	$V_{CE} = 10V$, $I_C = 50mA$, $f = 100MHz$
SWITCHING CHARACTERISTICS						
Turn-On Time	t _{on}		90		ns	
Delay Time	t _d		17		ns	
Rise Time	t _r		73		ns	V _{CC} = 10V
Turn-Off Time	t _{off}	17	300		ns	$I_C = 0.5A$, $I_{B1} = I_{B2} = 25mA$
Storage Time	ts	P 1 2	220		ns	
Fall Time	tf	7	80	7	ns	
					_	

Notes: 4. Measured under pulsed conditions. Pulse width = $300\mu s$. Duty cycle $\leq 2\%$.

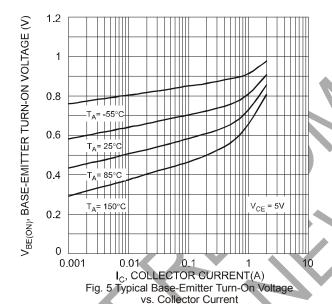


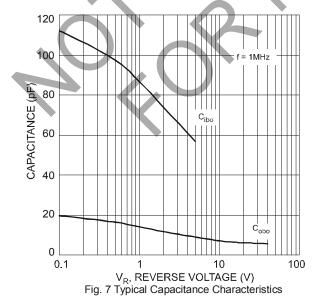












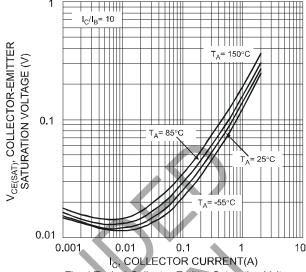


Fig. 4 Typical Collector-Emitter Saturation Voltage vs. Collector Current

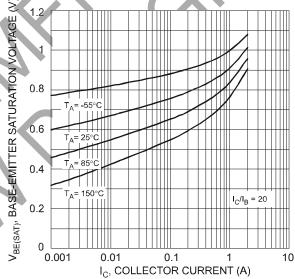
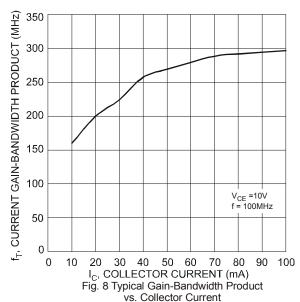


Fig. 6 Typical Base-Emitter Saturation Voltage vs. Collector Current



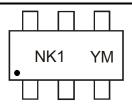


Ordering Information (Note 5)

Device	Packaging	Shipping
DNLS160V-7	SOT-563	3000/Tape & Reel

Notes: 5. For packaging details, go to our website at http://www.diodes.com/datasheets/ap02007.pdf.

Marking Information

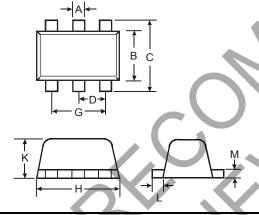


NK1 = Product Type Marking Code YM = Date Code Marking Y = Year ex: V = 2008 M = Month ex: 9 = September

Date Code Key

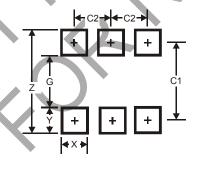
Year	2008		2009	2010		2011	2012		2013	2014		2015
Code	V		W	Х		Υ	Z		Α	В		С
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D

Package Outline Dimensions



- 100	w/	900	40000000			
SOT-563						
Dim	Min	Max	Тур			
Α	0.15	0.30	0.20			
В	1.10	1.25	1.20			
O	1.55	1.70	1.60			
D	-	-	0.50			
G	0.90	1.10	1.00			
Н	1.50	1.70	1.60			
K	0.55	0.60	0.60			
L	0.10	0.30	0.20			
M	0.10	0.18	0.11			
All	All Dimensions in mm					

Suggested Pad Layout



Dimensions	Value (in mm)
Z	2.2
G	1.2
Х	0.375
Υ	0.5
C1	1.7
C2	0.5

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